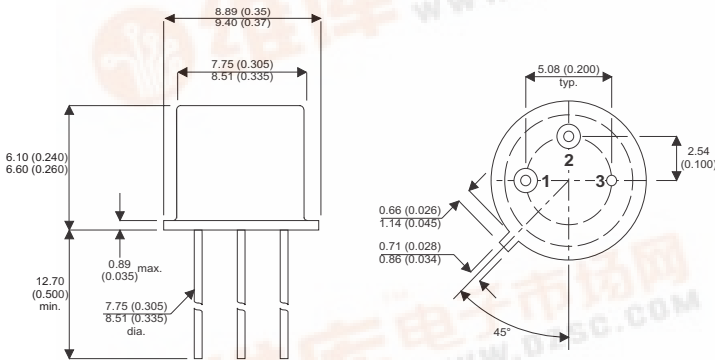


**BUY47**  
**BUY48**

**MECHANICAL DATA**

Dimensions in mm (inches)



**HIGH VOLTAGE, HIGH CURRENT  
SILICON EXPITAXIAL PLANAR  
NPN TRANSISTOR**

**APPLICATIONS**

Intended for High Voltage, High Current, Switching Applications up to 7A.

**TO-39 PACKAGE**

Pin 1 – Emitter      Pin 2 – Base      Pin 3 – Collector

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

			<b>BUY47</b>	<b>BUY48</b>
$V_{CBO}$	Collector – Base Voltage	( $I_E = 0$ )	150V	200V
$V_{CEO}$	Collector – Emitter Voltage	( $I_B = 0$ )	120V	170V
$V_{EBO}$	Emitter – Base Voltage	( $I_C = 0$ )		6V
$I_C$	Collector Current			7A
$I_{CM}$	Peak Collector Current (repetitive)			10A
$P_{tot}$	Total Power Dissipation	@ $T_{amb} \leq 25^{\circ}C$		1W
		@ $T_{case} \leq 50^{\circ}C$		10W
$T_{STG}$	Storage Temperature Range			-65 to +200°C
$T_J$	Maximum Operating Junction Temperature			200°C



**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$I_{CBO}$ Collector Cut-off Current	$V_{CB} = 80V$ $I_E = 0$	<b>BUY47</b>		10	$\mu A$	
		$T_C = 125^{\circ}C$		1	mA	
	$V_{CB} = 100V$ $I_E = 0$	<b>BUY48</b>		10	$\mu A$	
		$T_C = 125^{\circ}C$		1	mA	
$V_{(BR)CBO}^*$ Collector – Base Breakdown Voltage	$I_C = 1mA$ $I_E = 0$	<b>BUY47</b>		150	V	
		<b>BUY48</b>		200		
$V_{CEO(sus)}^*$ Collector – Emitter Sustaining Voltage	$I_C = 20mA$ $I_B = 0$	<b>BUY47</b>		120	V	
		<b>BUY48</b>		170		
$V_{EBO}^*$ Emitter – Base Voltage	$I_E = 1mA$ $I_C = 0$			6	V	
$V_{CE(sat)}^*$ Collector – Emitter Saturation Voltage	$I_C = 0.5A$ $I_B = 50mA$			0.05	V	
	$I_C = 2A$ $I_B = 0.2A$			0.45		
	$I_C = 5A$ $I_B = 0.5A$			1		
$V_{BE(sat)}^*$ Base – Emitter Saturation Voltage	$I_C = 0.5A$ $I_B = 50mA$			0.8	V	
	$I_C = 2A$ $I_B = 0.2A$			1.1		
	$I_C = 5A$ $I_B = 0.5A$			1.5		
$h_{FE}^*$ DC Current Gain	$I_C = 50mA$ $V_{CE} = 5V$			130	—	
	$I_C = 0.5A$ $V_{CE} = 5V$	40	150			
	$I_C = 2A$ $V_{CE} = 5V$	40	130			
	$I_C = 5A$ $V_{CE} = 5V$	15	45			
$f_T$ Transition Frequency	$I_C = 100mA$ $V_{CE} = 10V$			90	MHz	
$C_{CBO}$ Collector – Base Capacitance	$I_E = 0$ $f = 1MHz$	$V_{CB} = 50V$		45	80	$\mu F$
$t_{on}$ Turn-On Time	$I_C = 5A$ $V_{CC} = 40V$			1	$\mu s$	
$t_{off}$ Fall Time	$I_{B1} = -I_{B2} = 0.5A$			2		

**NOTES**

\* Pulse Test:  $t_p = 300\mu s$ ,  $\delta = 1.5\%$